

100 V, 6 A NPN high power bipolar transistor

26 January 2015

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61006PY

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	100	V
I _C	collector current			-	-	6	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	12	А
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_C &= 6 \text{ A}; I_B = 600 \text{ mA}; t_p \leq 300 \mu\text{s}; \\ \delta &\leq 0.02; T_{amb} = 25 ^\circ\text{C}; \text{ pulsed} \end{split}$		-	35	57	mΩ



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	C
2	Е	emitter		в
3	E	emitter	a	- M
4	В	base	មុច្ចថ្	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	571125

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PHPT61006NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT61006NY	1006NAB

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	6	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	12	А
I _B	base current			-	1	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

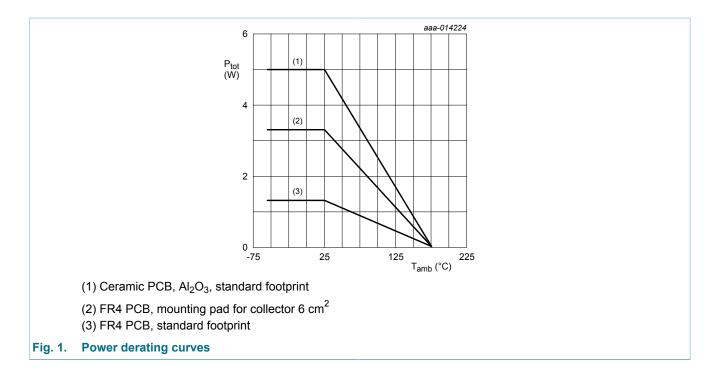
[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².

[3] Device mounted on an ceramic PCB; Al₂O₃, standard footprint.

[4] Power dissipation from junction to mounting base.

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9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance	in free air	[1]	-	-	115	K/W
		[2]	-	-	45	K/W	
	ambient		[3]	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

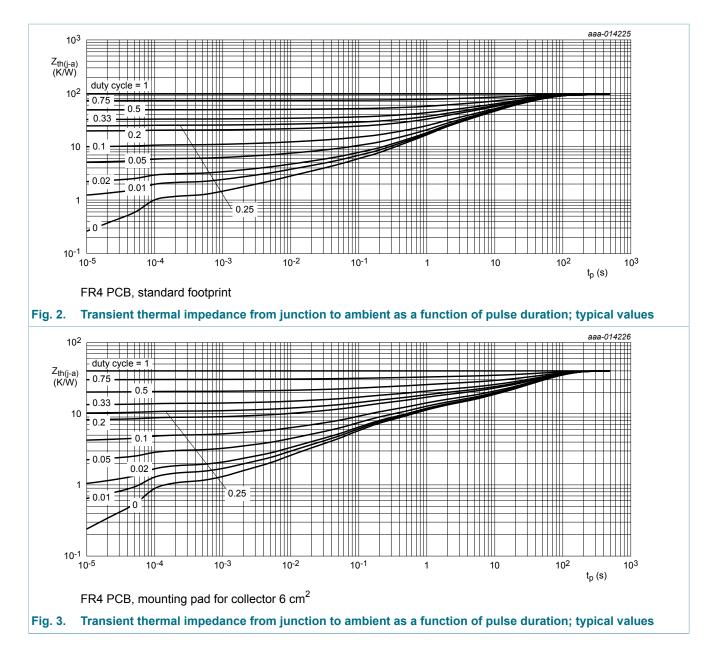
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

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10. Characteristics

Table 7. Cl	haracteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
current		V_{CB} = 80 V; I _E = 0 A; T _j = 150 °C		-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 80 V; V_{BE} = 0 V; T_{amb} = 25 °C		-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C		-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C		140	260	-	
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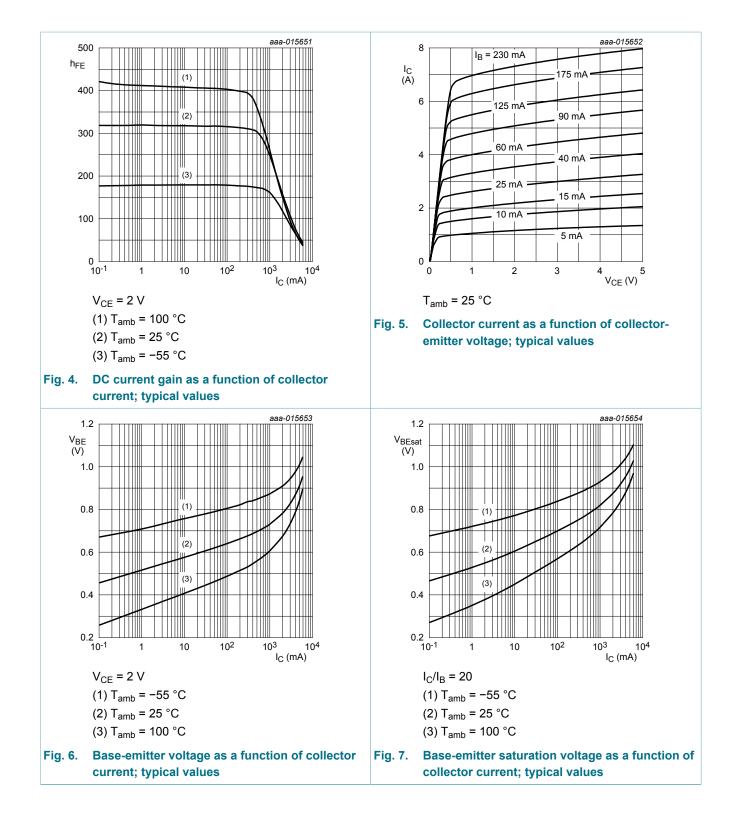
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V_{CE} = 2 V; I_C = 1 A; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	120	210	-	
		V_{CE} = 2 V; I_C = 3 A; $t_p \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	50	90	-	
		$V_{CE} = 2 \text{ V; } I_C = 6 \text{ A; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02; \text{ T}_{amb} = 25 \text{ °C; pulsed}$	25	40	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	45	65	mV
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	150	mV
		I_{C} = 6 A; I_{B} = 600 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	210	340	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 6 A; I_{B} = 600 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	35	57	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	0.85	1	V
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1.05	1.3	V
		I_{C} = 6 A; I_{B} = 600 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	1.1	1.3	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	-	0.7	0.9	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 3 A; I _{Bon} = 150 mA;	-	10	-	ns
t _r	rise time	I _{Boff} = -150 mA; T _{amb} = 25 °C	-	365	-	ns
t _{on}	turn-on time	-	-	375	-	ns
t _s	storage time	-	-	285	-	ns
t _f	fall time	-	-	385	-	ns
t _{off}	turn-off time	-	-	670	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 500 mA; f = 100 MHz; T _{amb} = 25 °C	-	170	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	22	-	pF

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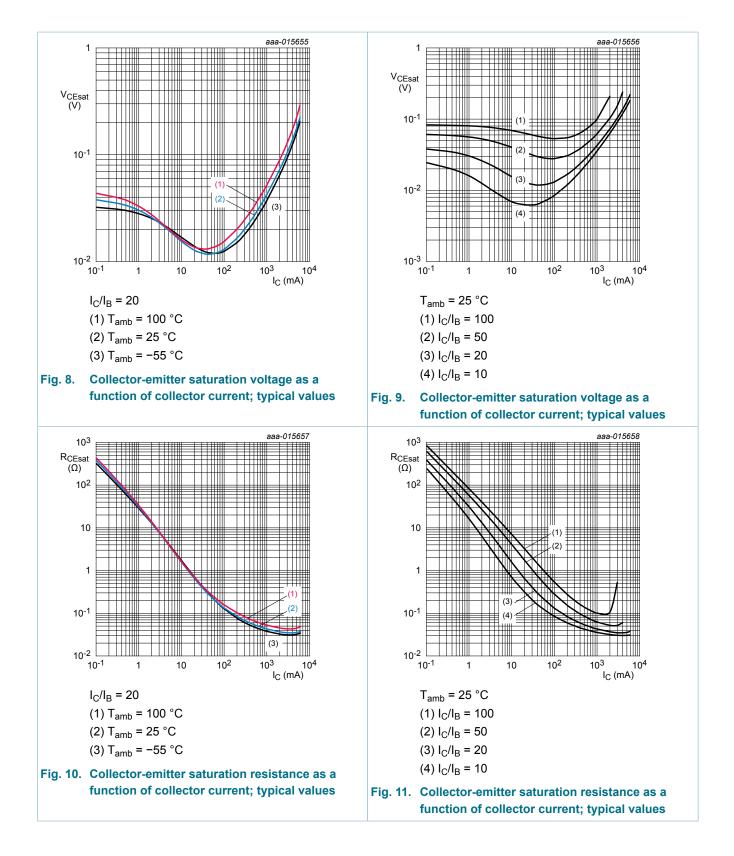


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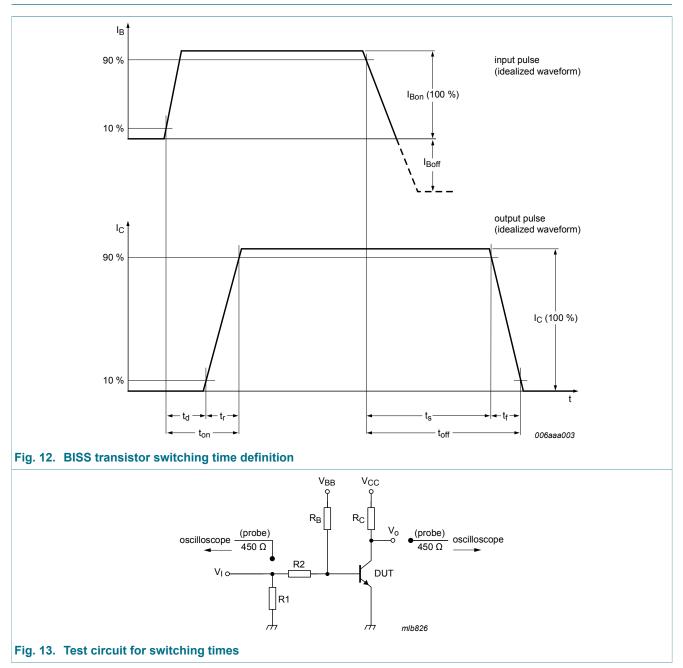
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11. Test information

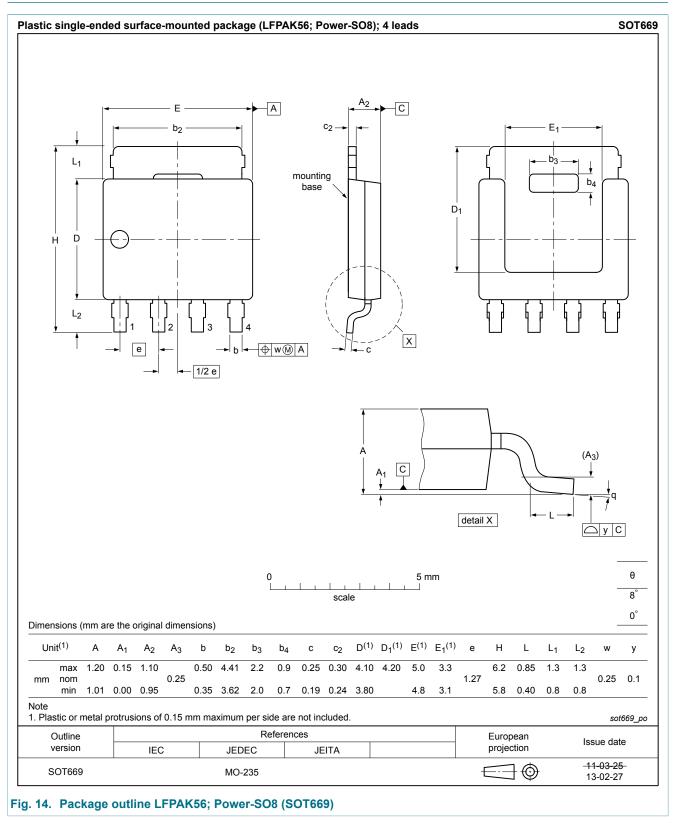


This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



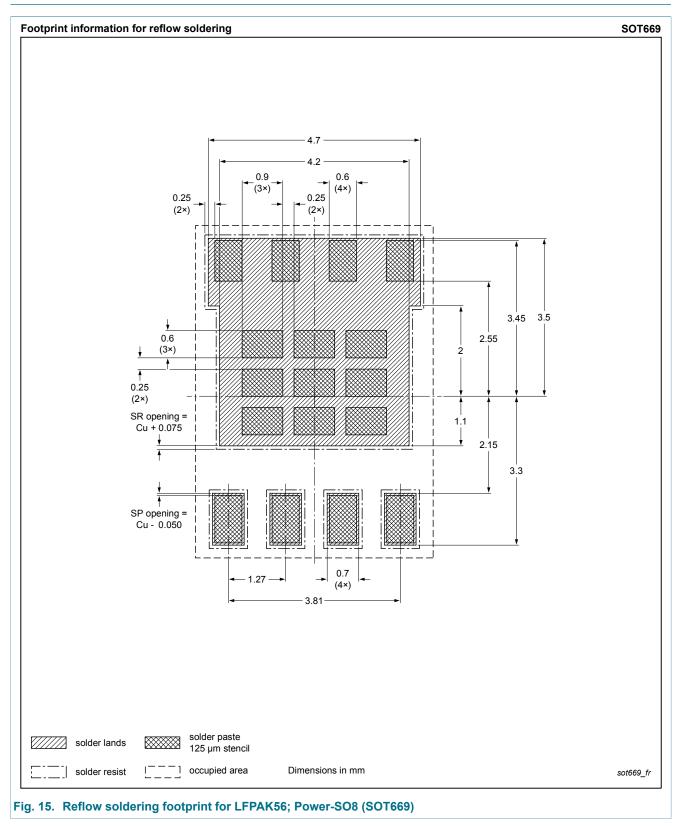
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13. Soldering



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14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PHPT61006NY v.1	20150126	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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